

### **Description**

The HCJ3139K uses advanced trench technology

to provide excellent R<sub>DS(ON)</sub>, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



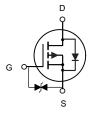
#### SOT-723

#### **General Features**

 $V_{DS} = -20V I_{D} = -0.66A$ 

 $R_{DS(ON)}$  < 560 m $\Omega$ @  $V_{GS}$ = -4.5V

ESD Rating: 1500V HBM



#### P-Channel MOSFET

## **Application**

Load/Power Switching

Interfacing Switching

Battery Management for Ultra Small Portable Electronics

## **Package Marking and Ordering Information**

| Product ID | Pack    | Marking | Qty(PCS) |
|------------|---------|---------|----------|
| HCJ3139K   | SOT-723 | KD      | 8000     |

### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

| Symbol                           | Parameter  | Limit      | Unit       |
|----------------------------------|--|------------|------------|
| V <sub>DS</sub>                  | Drain-Source Voltage                             | -20        | V          |
| V <sub>G</sub> s                 | Gate-Source Voltage                              | ±10        | V          |
| I <sub>D</sub>                   | Drain Current-Continuous                         | -0.66      | A          |
| Ідм                              | Drain Current-Pulsed (Note 1)                    | -1.2       | A          |
| P <sub>D</sub>                   | Maximum Power Dissipation                        | 0.15       | W          |
| T <sub>J</sub> ,T <sub>STG</sub> | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}$ |
| ReJA                             | Thermal Resistance, Junction-to-Ambient (Note 2) | 850        | °C/W       |



## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

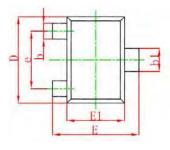
| Parameter  | Symbol               | Test conditions   | Min  | Тур  | Max  | Unit |
|--|----------------------|---|------|------|------|------|
| Drain-source breakdown voltage                           | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA  | -20  |      |      | V    |
| Zero gate voltage drain current                          | I <sub>DSS</sub>     | V <sub>DS</sub> =-20V,V <sub>GS</sub> = 0V  |      |      | -1   | μA   |
| Gate-body leakage current                                | I <sub>GSS</sub>     | V <sub>GS</sub> =±10V, V <sub>DS</sub> = 0V   |      |      | ±10  | μA   |
| Gate threshold voltage (note2)                           | V <sub>GS(th)</sub>  | V <sub>DS</sub> =VGS, I <sub>D</sub> =-250μA  | -0.4 | -0.7 | -1.0 | V    |
| Dunin annua an anaistean                                 | R <sub>DS(on)</sub>  | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.5A   |      |      | 0.56 | Ω    |
| Drain-source on-resistance (note2)                       |                      | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.2A   |      |      | 0.78 | Ω    |
| Maximum Continuous Drain to Source Diode Forward Current | Is                   |   |      |      | -0.6 | А    |
| Maximum Pulsed Drain to Source Diode Forward Current     | I <sub>SM</sub>      |   |      |      | -1.2 | Α    |
| Diode forward voltage                                    | V <sub>SD</sub>      | I <sub>S</sub> =-0.5A, V <sub>GS</sub> = 0V   |      |      | -1.2 | V    |
| Input capacitance  | C <sub>iss</sub>     | V <sub>DS</sub> =-16V,V <sub>GS</sub> =0V,<br>f =1MHz                                 |      | 115  |      | pF   |
| Output capacitance                                       | Coss                 |   |      | 15   |      | pF   |
| Reverse transfer capacitance                             | Crss                 | 1 - 11VII 12  |      | 9    |      | pF   |
| Turn-on delay time (note3)                               | t <sub>d(on)</sub>   |   |      | 9    |      | nS   |
| Turn-on rise time (note3)                                | t <sub>r</sub>       | $V_{GS}$ =-4.5 $V$ , $V_{DS}$ =-10 $V$ ,<br>$I_D$ =-200 $mA$ , $R_{GEN}$ =10 $\Omega$ |      | 6    |      | nS   |
| Turn-off delay time (note3)                              | t <sub>d(off)</sub>  |   |      | 33   |      | nS   |
| Turn-off fall time (note3)                               | <b>t</b> f           |   |      | 22   |      | nS   |

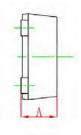
#### Notes:

- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test: Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.

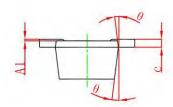


# **SOT-723 Package Outline Dimensions**

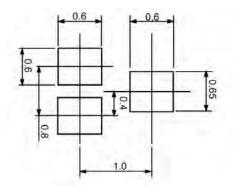




| Symbol | Dimensions In Millimet |      |  |  |
|--------|------------------------|------|--|--|
| Symbol | Min                    | Max  |  |  |
| Α      | 0.42                   | 0.50 |  |  |
| A1     | 0.00                   | 0.05 |  |  |
| b      | 0.16                   | 0.28 |  |  |
| b1     | 0.25                   | 0.35 |  |  |
| С      | 0.07                   | 0.16 |  |  |
| D      | 1.10                   | 1.30 |  |  |
| е      | 0.8TYP                 |      |  |  |
| E      | 1.10                   | 1.30 |  |  |
| E1     | 0.75 0.85              |      |  |  |
| θ      | 8° 10°                 |      |  |  |



# Suggested Pad Layout (mm)



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